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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Yoshihisa Nagano et al. : Art Unit: 2815
Serial No.: 09/103,873 : Examiner: J. Diaz
Filed: June 24, 1998 **Expedited Procedure**
For: SEMICONDUCTOR DEVICE AND METHOD **37 C.F.R. § 1.116**
FOR FABRICATING THE SAME

AMENDMENT

FAX RECEIVED

Assistant Commissioner for Patents
Washington, DC 20231

TECHNOLOGY CENTER 2800

SIR:

Responsive to the Official Action dated September 24, 2002, please amend the above-identified application as follows:

CLAIMS:

Please cancel claims 3 and 5.

Please replace claims 1 and 32 with the following amended claims:

1. (As Amended) A semiconductor device, comprising:

a capacitor provided on a supporting substrate having an integrated circuit thereon and including a lower electrode, a dielectric film, and an upper electrode, said dielectric film being formed from either a dielectric material having a high dielectric constant or a ferroelectric material;

a first interlayer insulating film provided so as to directly cover the capacitor;

a first interconnect selectively provided on the first interlayer insulating film and electrically connected to the integrated circuit and the capacitor through a first contact hole formed in the first interlayer insulating film;